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With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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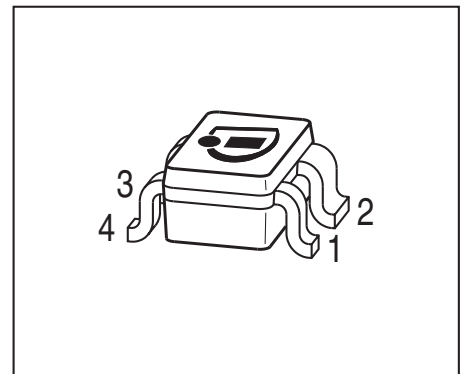
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High Performance Bipolar NPN RF Transistor

- High transducer gain of typ. 14 dB @ 25 mA, 6 GHz
- Low minimum noise figure of typ. 0.85 dB @ 6GHz
- High output compression of typ. 11 dBm @ 25 mA
- Pb-free (RoHS compliant) package
- For a wide range of non-automotive applications
 - 2nd and 3rd LNA stage and mixer stage in LNB
 - 5.8 GHz analog/digital cordless phone
 - Satellite radio SDARS
 - WLAN, WiMAX, UWB



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BF888	RYs	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
$T_A = 25\text{ }^\circ\text{C}$		4.0	
$T_A = -55\text{ }^\circ\text{C}$		3.5	
Collector-emitter voltage	V_{CES}	13	
Collector-base voltage	V_{CBO}	13	
Emitter-base voltage	V_{EBO}	1.2	
Collector current	I_C	30	mA
Base current	I_B	3	
Total power dissipation ¹⁾	P_{tot}	160	mW
$T_S \leq 89\text{ }^\circ\text{C}$			
Junction temperature	T_J	150	$^\circ\text{C}$
Ambient temperature	T_A	-55 ... 150	
Storage temperature	T_{Std}	-55 ... 150	

¹⁾ T_S is measured on the emitter lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 380	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4	4.7	-	V
Collector-emitter cutoff current $V_{CE} = 5 \text{ V}, V_{BE} = 0$	I_{CES}	-	1	-	nA
Collector-base cutoff current $V_{CB} = 5 \text{ V}, I_E = 0$	I_{CBO}	-	1	-	
Emitter-base cutoff current $V_{EB} = 0.5 \text{ V}, I_C = 0$	I_{EBO}	-	10	-	
DC current gain $I_C = 25 \text{ V}, V_{CE} = 3 \text{ V}, \text{ pulse measured}$	h_{FE}	-	250	-	-

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

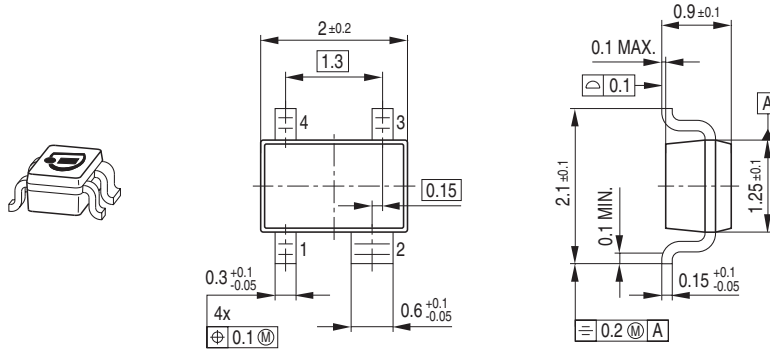
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 25\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 2\text{ GHz}$	f_T	-	47	-	GHz
Collector-base capacitance $V_{CB} = 3\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.08	-	pF
Collector emitter capacitance $V_{CE} = 3\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.35	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.45	-	
Noise figure $I_C = 8\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$ $I_C = 8\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 6\text{ GHz}$, $Z_S = Z_{Sopt}$	F	-	0.5 0.85	-	dB
Power gain $I_C = 25\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ms}	-	27	-	dB
Power gain, maximum available ¹⁾ $I_C = 25\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 6\text{ GHz}$	G_{ma}	-	17	-	dB
Transducer gain $I_C = 25\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 1.8\text{ GHz}$ $f = 6\text{ GHz}$	$ S_{21e} ^2$	-	24.5 14	-	dB
Third order intercept point at output ²⁾ $V_{CE} = 3\text{ V}$, $I_C = 25\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\ \Omega$	IP_3	-	25	-	dBm
1dB Compression point $I_C = 25\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	11	-	

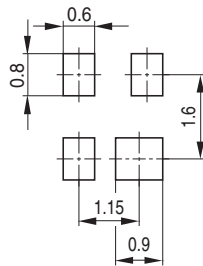
$$^1G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$$

²⁾IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50 Ω from 0.1 MHz to 6 GHz

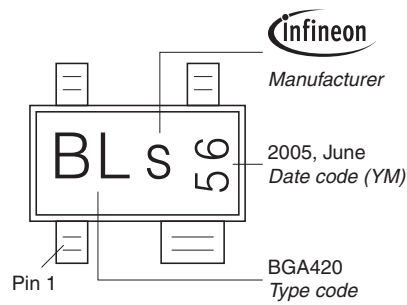
Package Outline



Foot Print

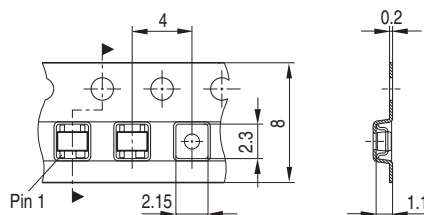


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



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